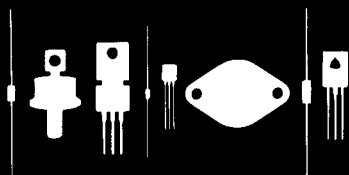


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145 Adams Avenue
Hauppauge, New York 11788



1N485B
1N486B

SILICON DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N485B, 1N486B types are silicon planar diodes designed for low leakage applications.

MAXIMUM RATINGS (T_A = 25°C)

	SYMBOL	1N485B	1N486B	UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	200	250	V
Peak Working Reverse Voltage	V _{RWM}	180	225	V
Average Forward Current	I _O	200	200	mA
Forward Steady-State Current	I _F	500	500	mA
Peak Repetitive Forward Current	I _{FM}	600	600	mA
Peak Forward Surge Current (1.0μs pulse)	I _{FSM}	4.0	4.0	A
Peak Forward Surge Current (1.0s pulse)	I _{FSM}	1.0	1.0	A
Power Dissipation	P _D	500	500	mW
Operating and Storage				
Junction Temperature	T _J , T _{stg}	-65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	1N485B		1N486B		UNITS
		MIN	MAX	MIN	MAX	
BV _R	I _R = 100μA	200		250		V
I _R	V _R = Rated V _{RWM}		25		50	nA
I _R	V _R = Rated V _{RWM} , T _A = 150°C		5.0		10	μA
V _F	I _F = 100mA		1.0		1.0	V

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